

agreement with predictions of Sec.2. In particular, the minimal value of resistance increases with temperature decrease for Mott type hopping and decreases for the Coulomb gap hopping. As it was noted in the Introduction, the agreement was strongly improved when we had taken into account more subtle spin effects [7], however here we will not go into these details discussed earlier.

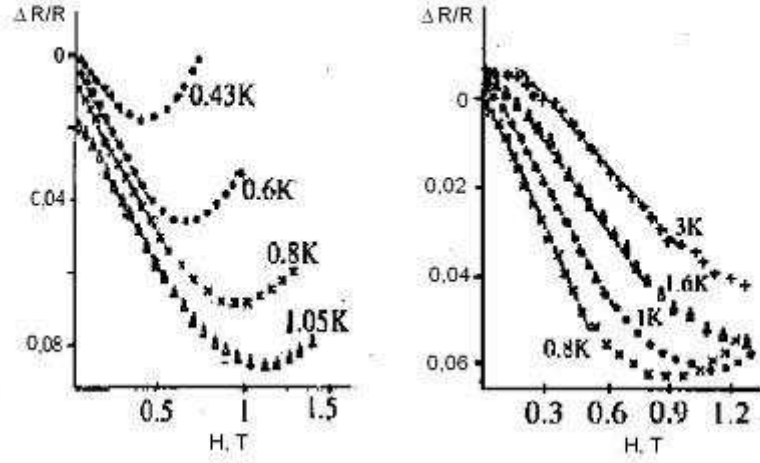


FIG. 1: Temperature behavior of magnetoresistance for bulk CdTe crystals doped by donor impurities (Cl). Fig. 1,a - the curves for the sample in the Coulomb gap regime, Fig.1, b - for the sample in the Mott regime.

At Figs. 2,3 we present experimental results described in [11], [12] for p-GaAs/AlGaAs:Be